



# Collective Dynamics and Memory-Induced Long-Range Order in Thermal Neuristor Networks

Yuan-Hang Zhang

Y.-H. Zhang, C. Sipling, E. Qiu, I.K. Schuller, M. Di Ventra

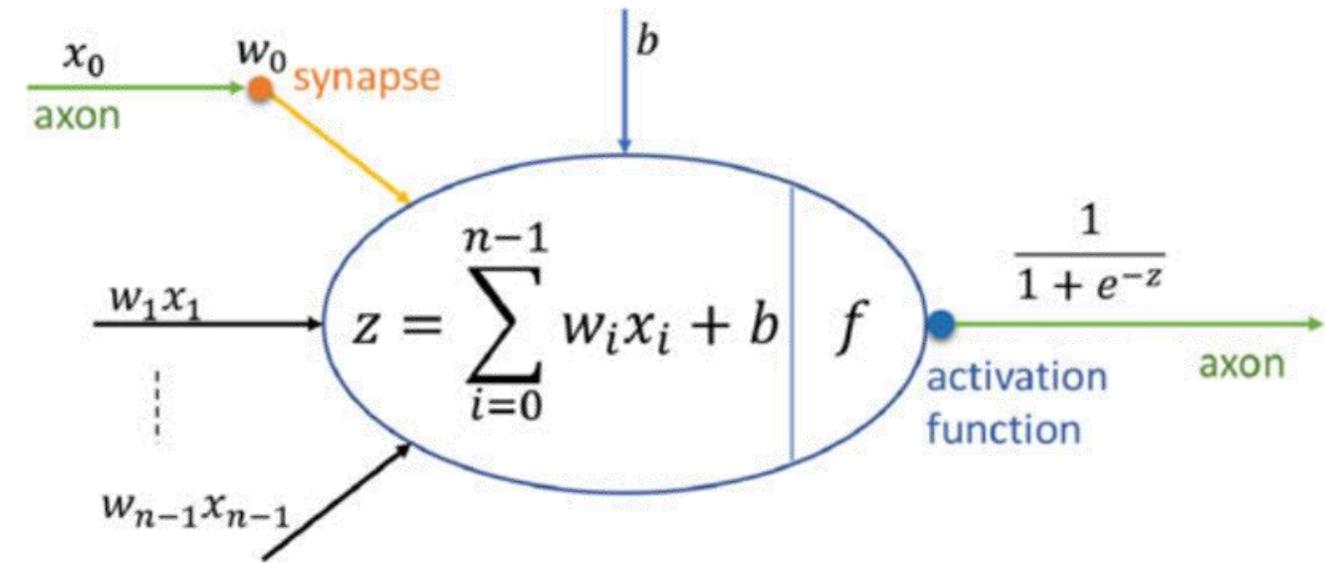
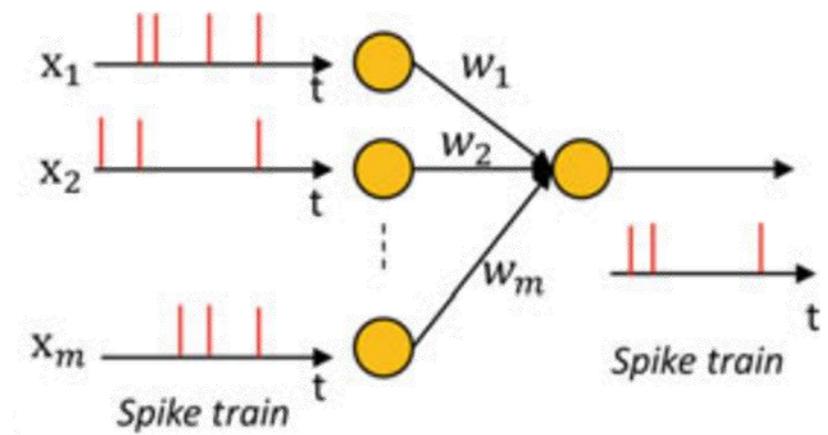
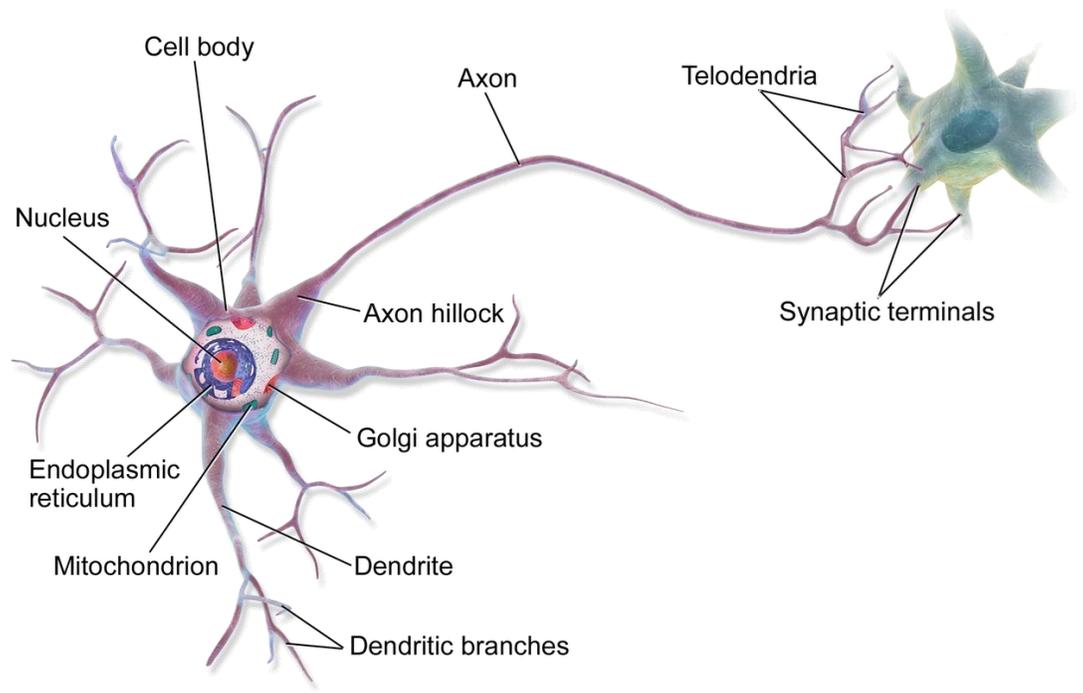
arXiv:2312.12899



UC San Diego



# Neuromorphic computing





# Vanadium Dioxide

Insulator-to-metal transition:  $T_c \approx 340K$

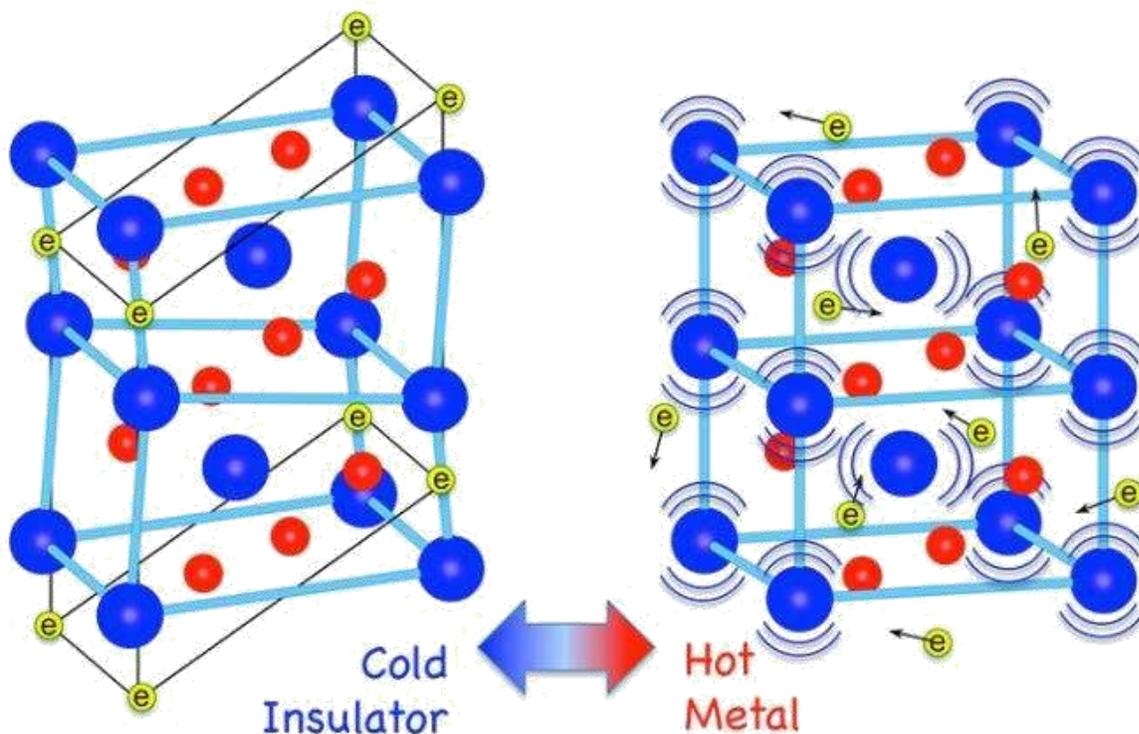
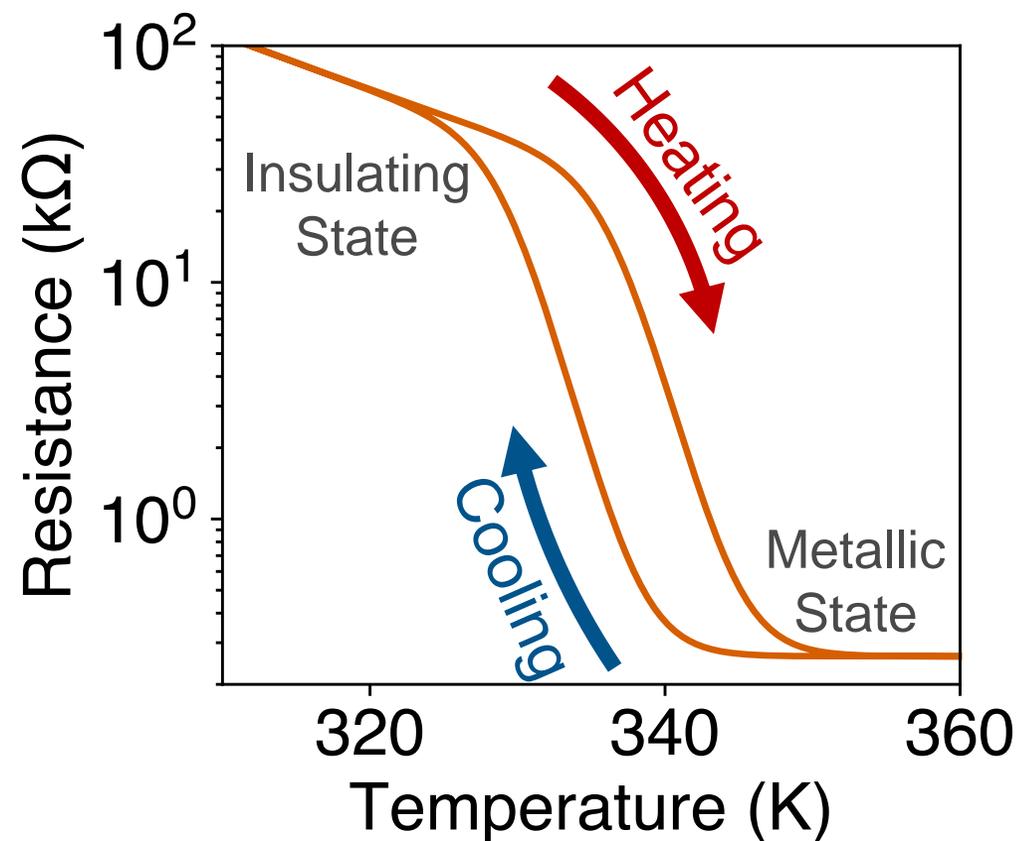


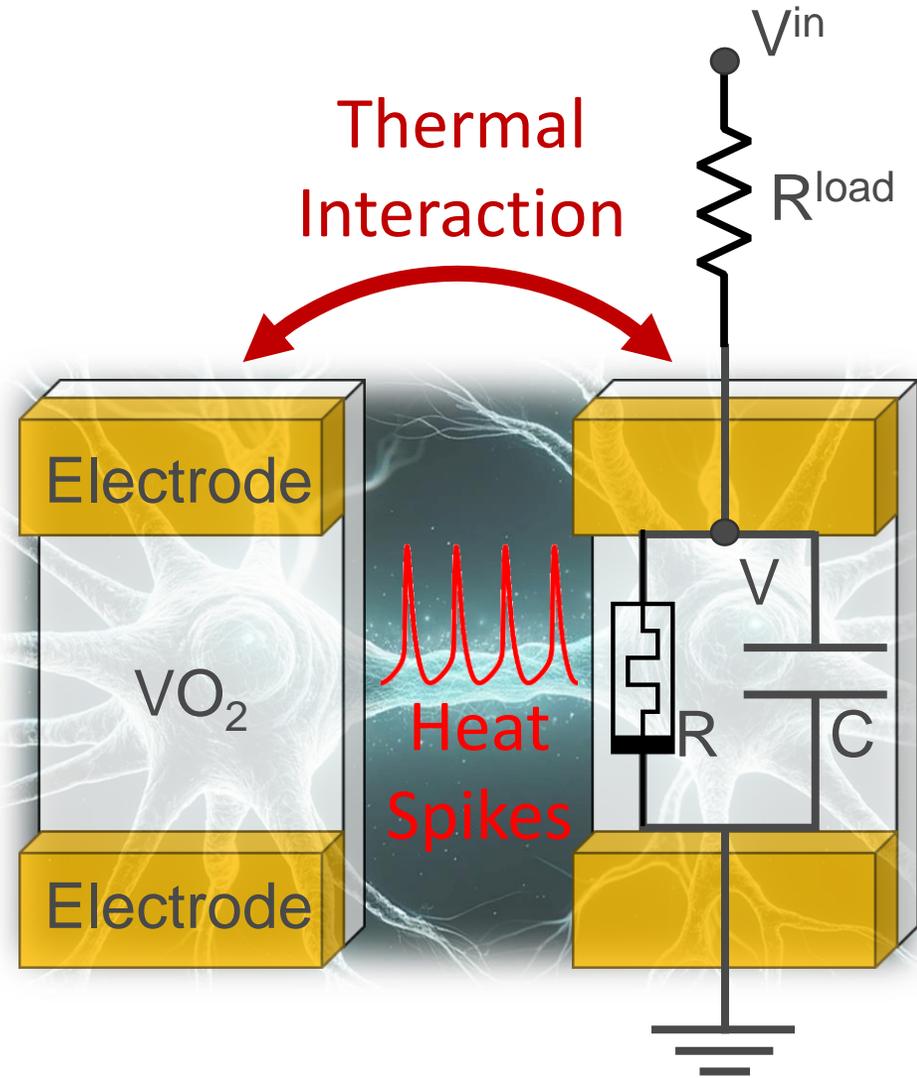
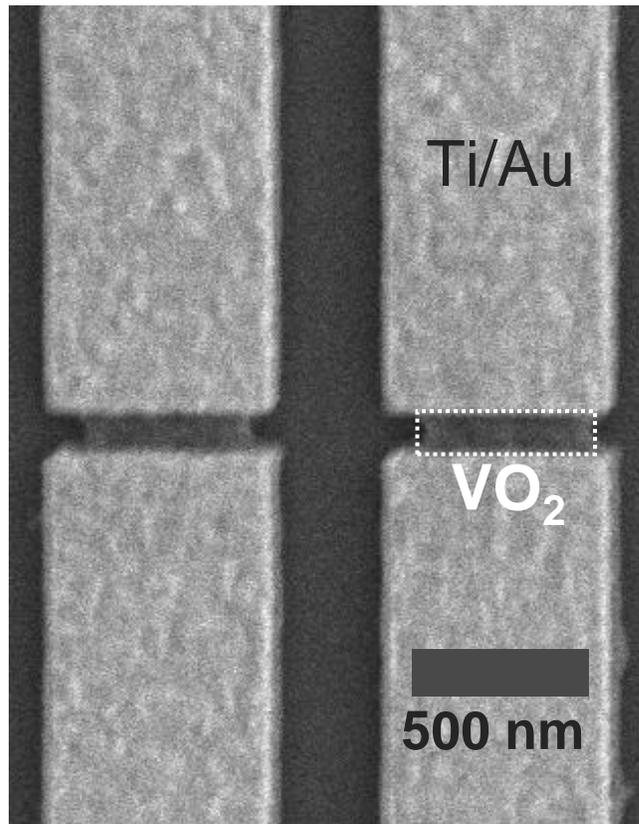
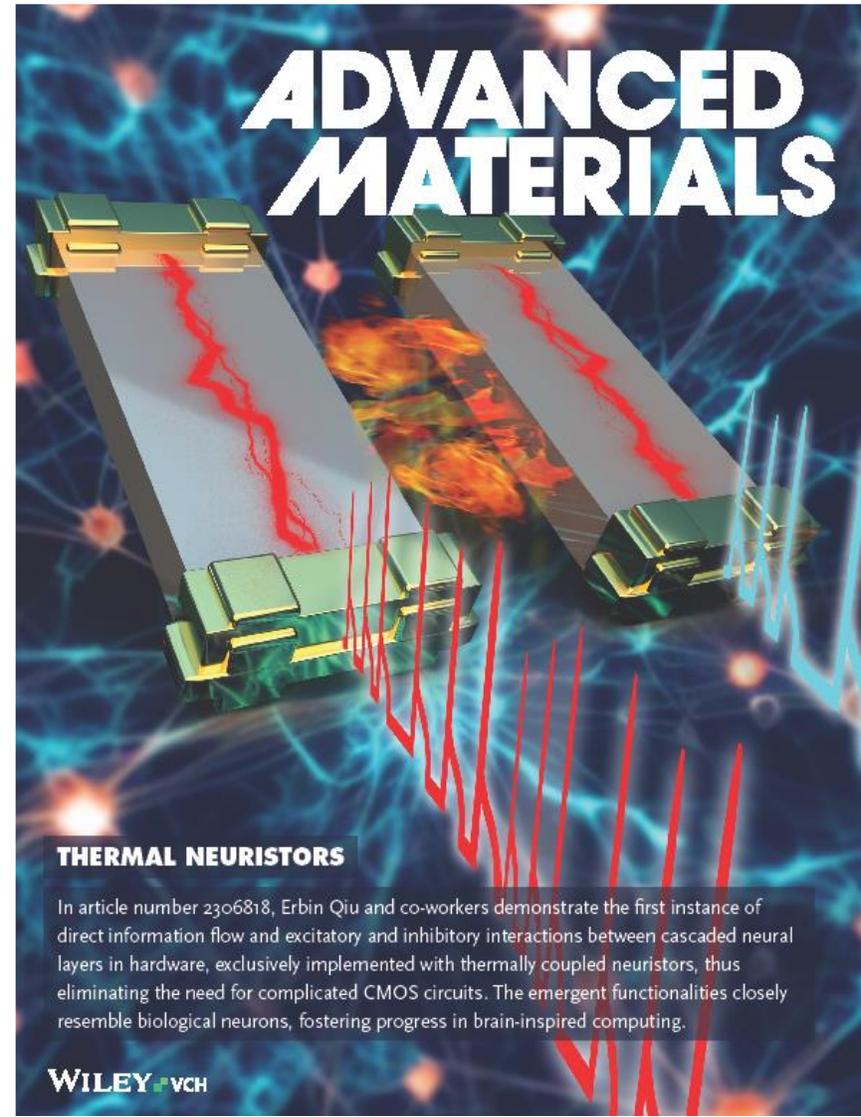
Image credit: <https://phys.org/news/2015-04-insulator-to-metal-transition-vanadium-dioxide.html>



Budai, J. D., Hong, J., Manley, M. E., Specht, E. D., Li, C. W., Tischler, J. Z., ... & Delaire, O. (2014). Metallization of vanadium dioxide driven by large phonon entropy. *Nature*, 515(7528), 535-539.



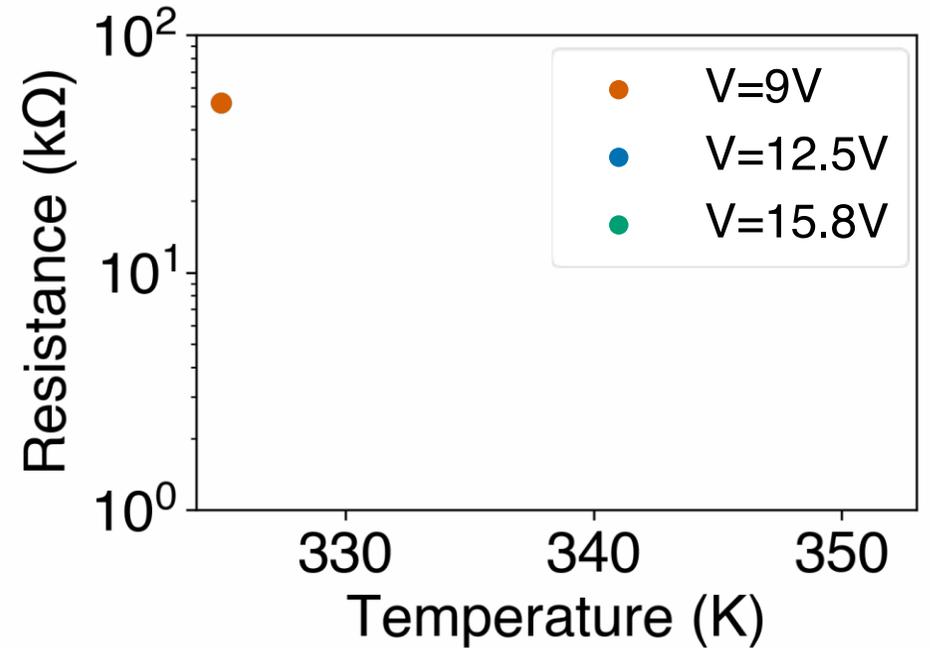
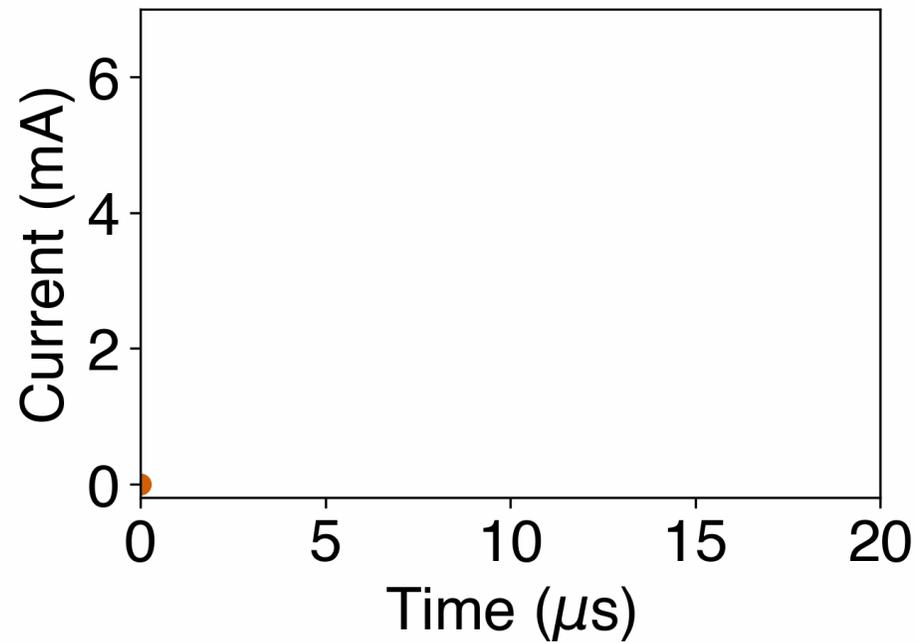
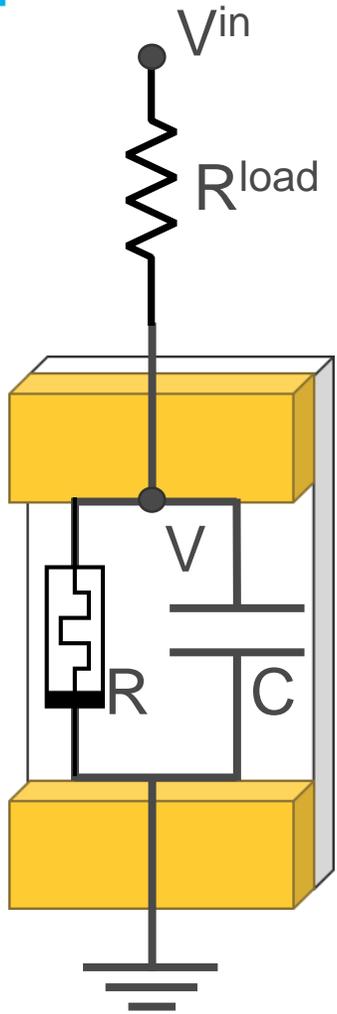
# Thermal Neuristor



Qiu, E., Zhang, Y. H., Di Ventra, M., & Schuller, I. K. (2023). Reconfigurable cascaded thermal neuristors for neuromorphic computing. *Advanced Materials*, 2306818.

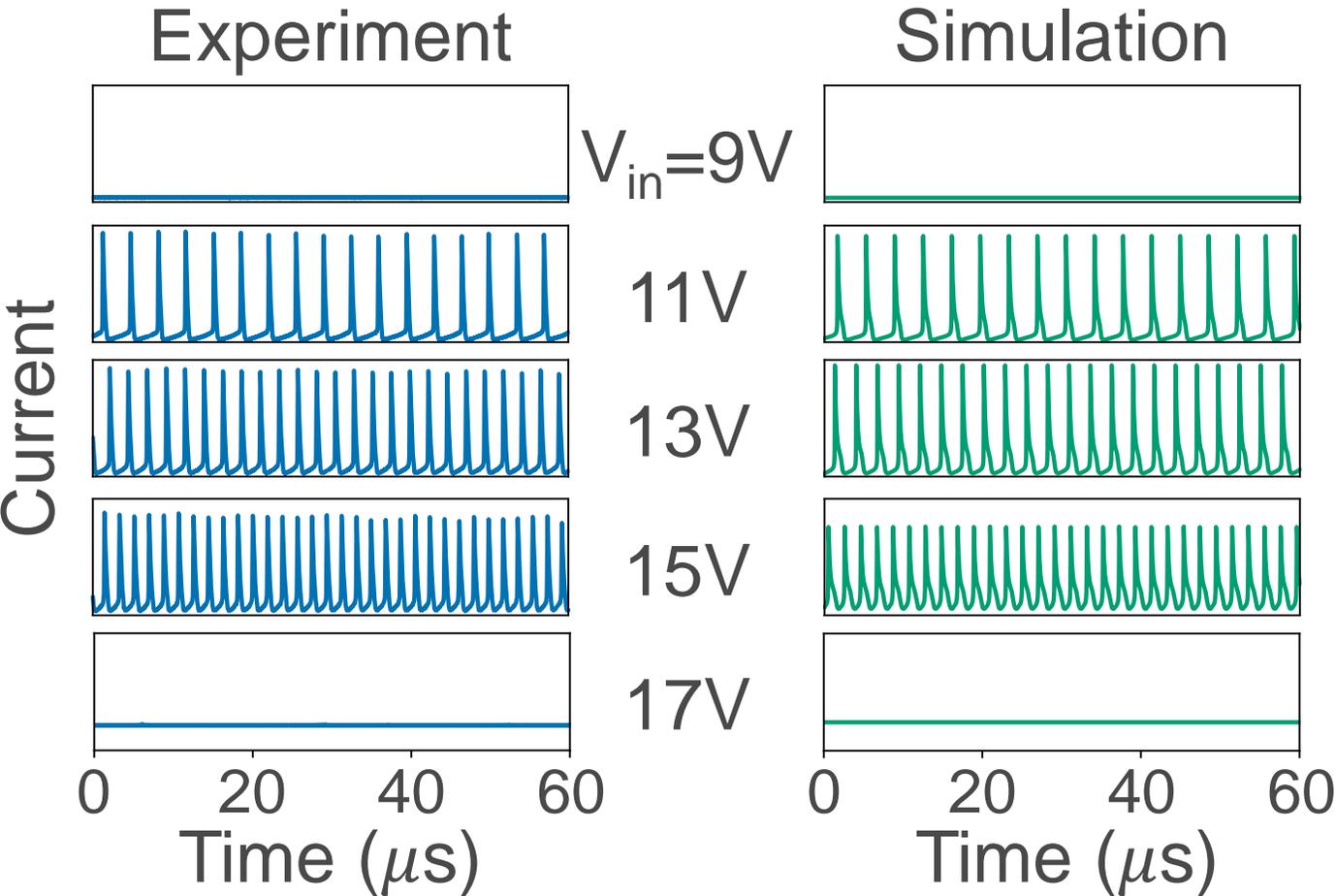


# Single Neuristor Characteristics



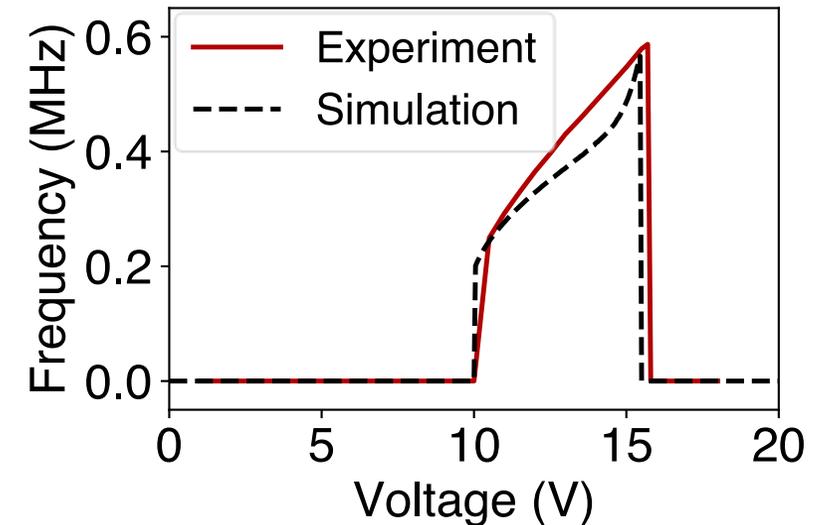


# Single Neuristor Characteristics



$$C \frac{dV}{dt} = \frac{V_{in}}{R_{load}} - V \left( \frac{1}{R_{VO_2}} + \frac{1}{R_{load}} \right)$$

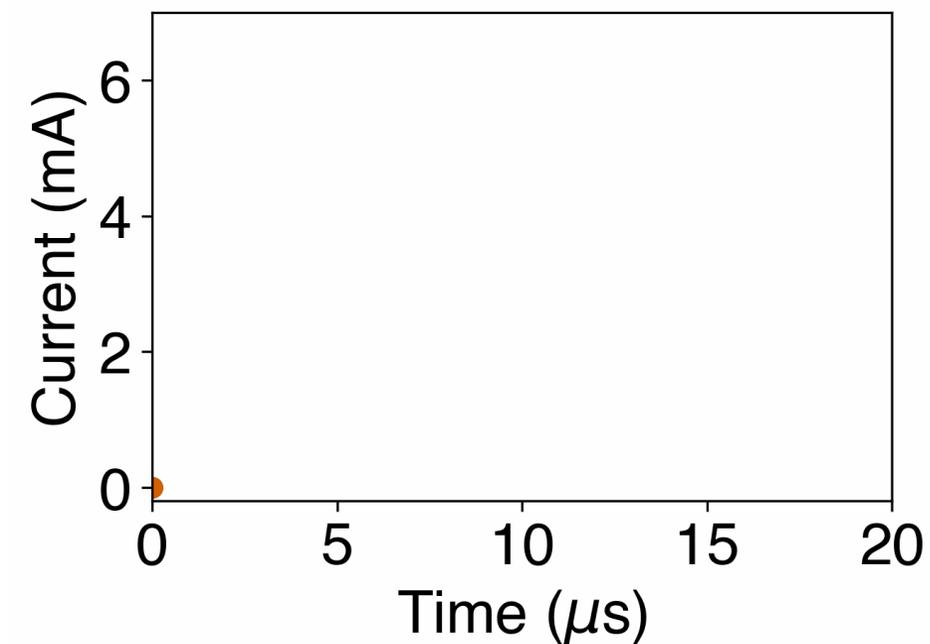
$$C_{th} \frac{dT}{dt} = \frac{V^2}{R_{VO_2}} - S_{env}(T - T_0)$$



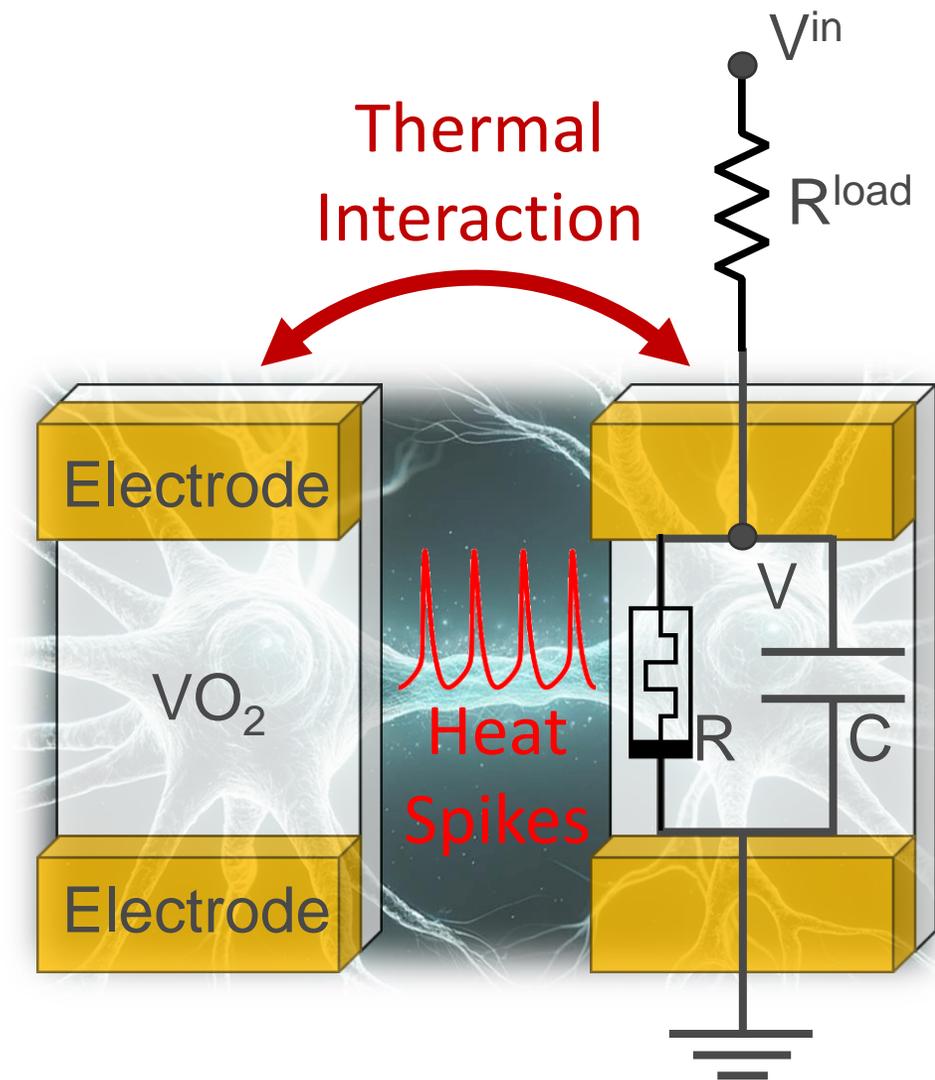
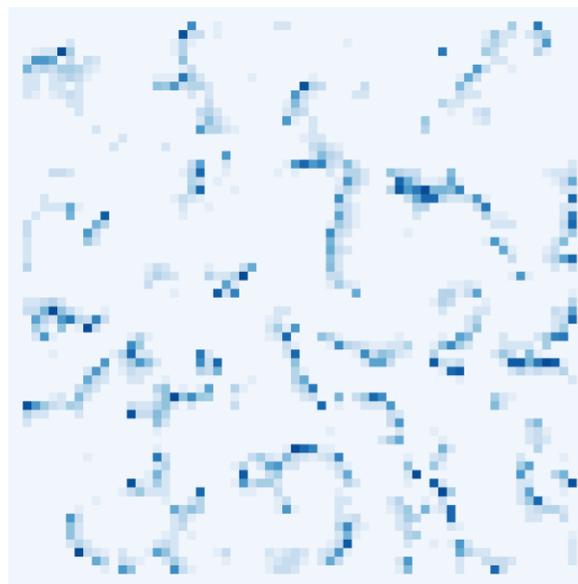


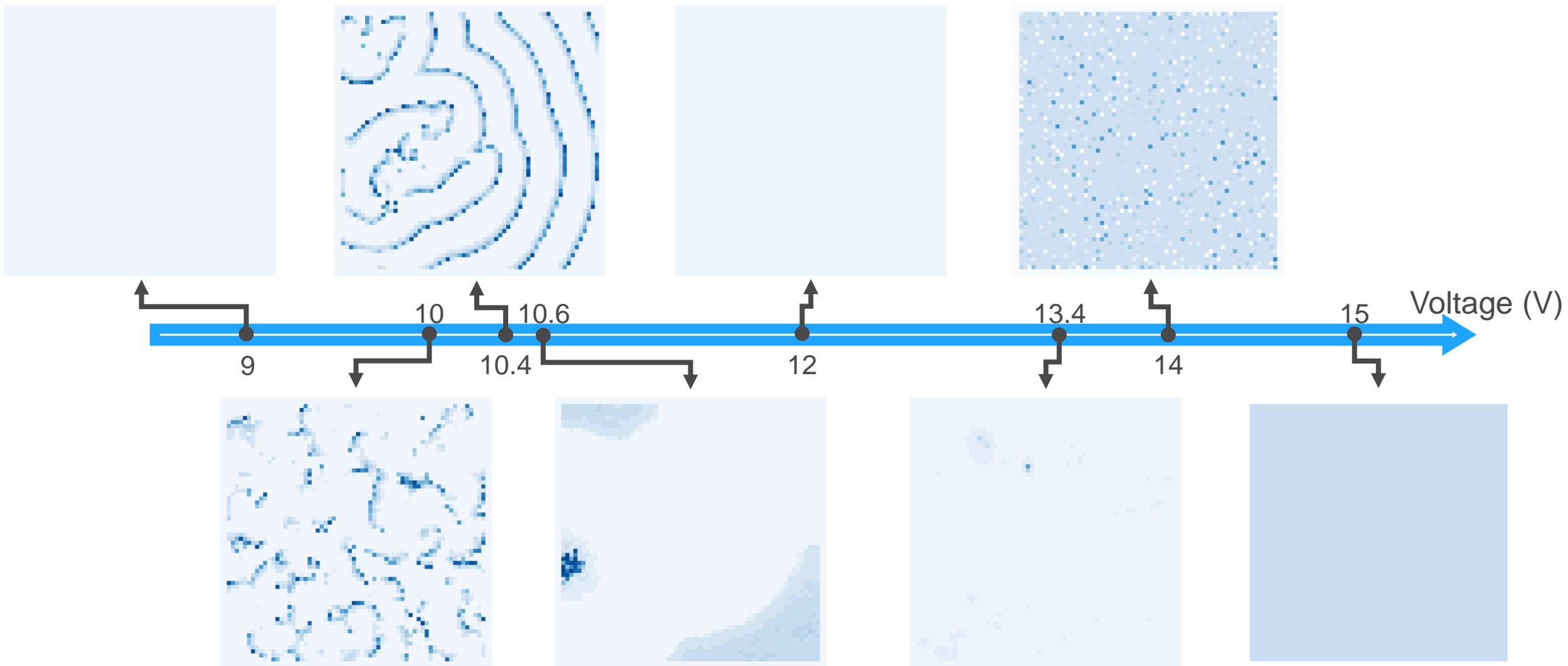
# Thermal Neuristor Array

1 neuron



64x64 neurons

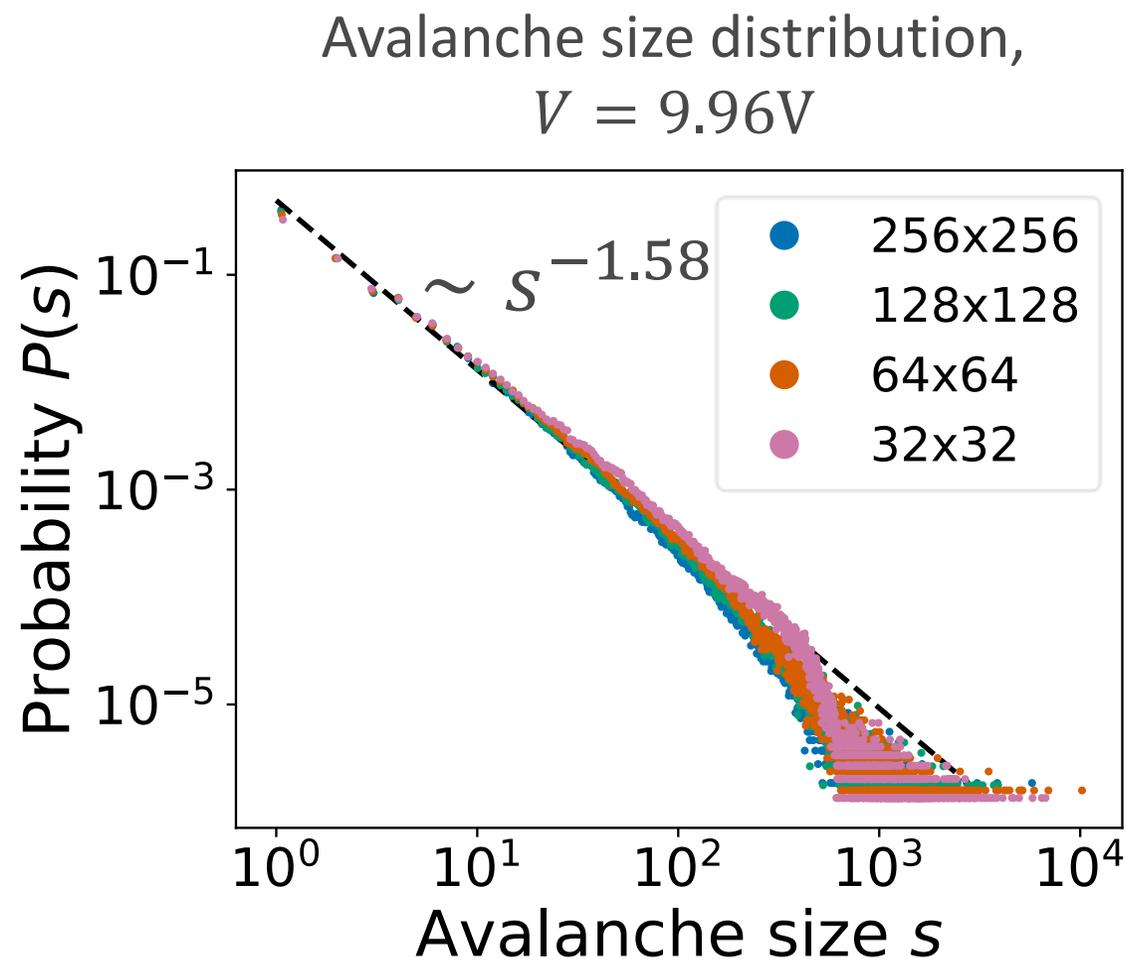
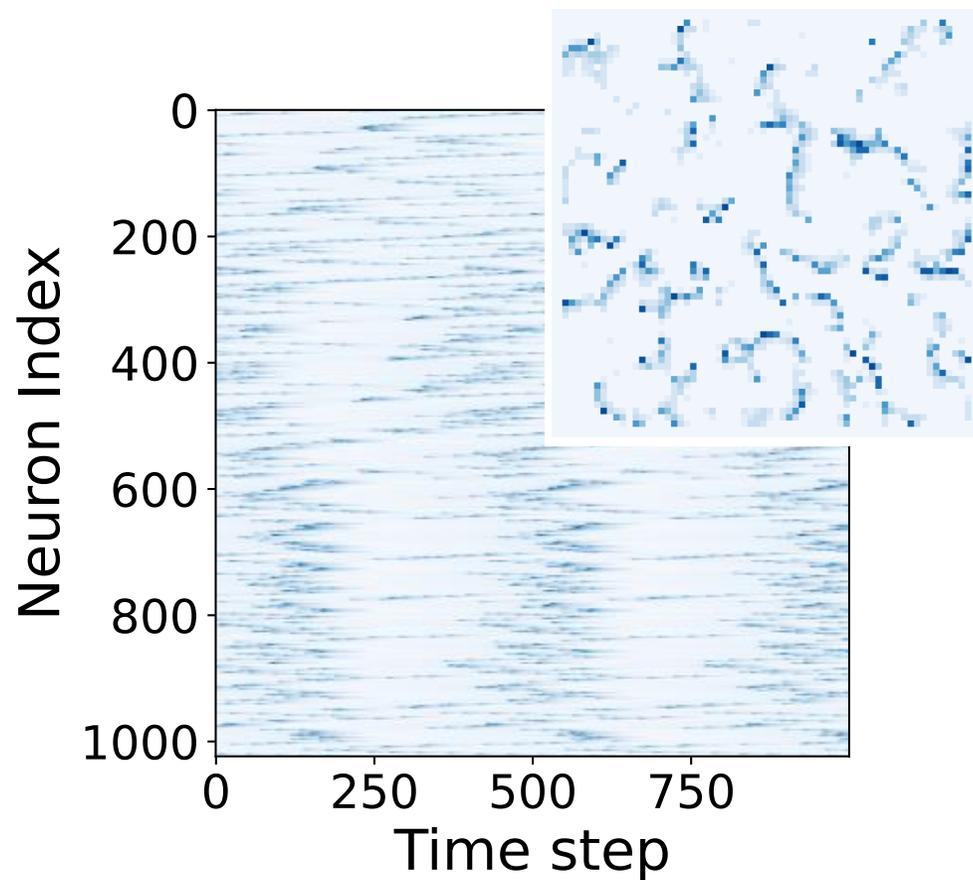


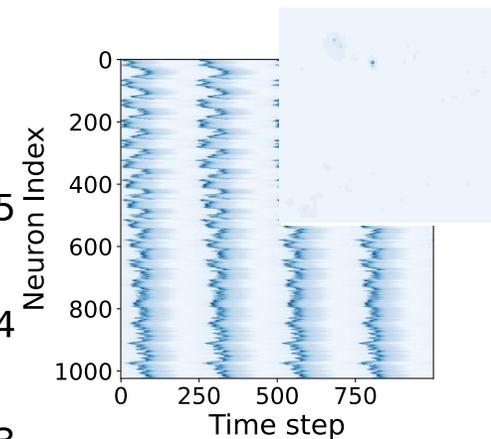
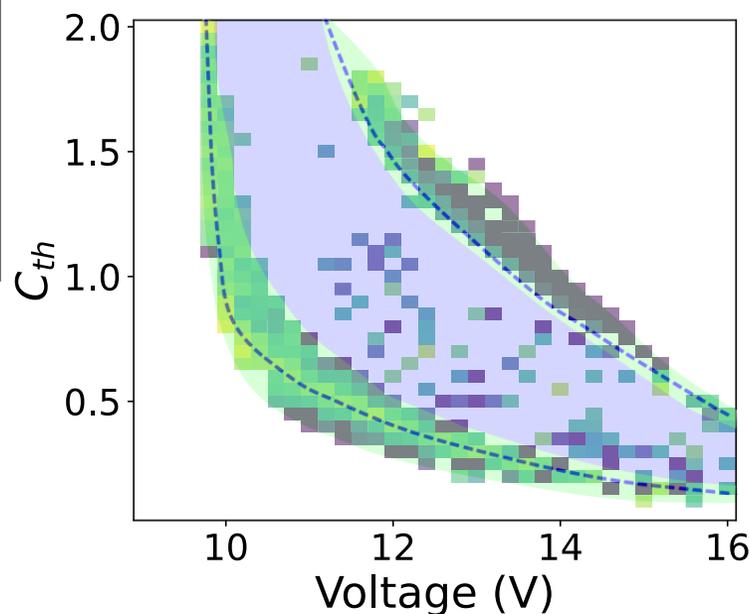
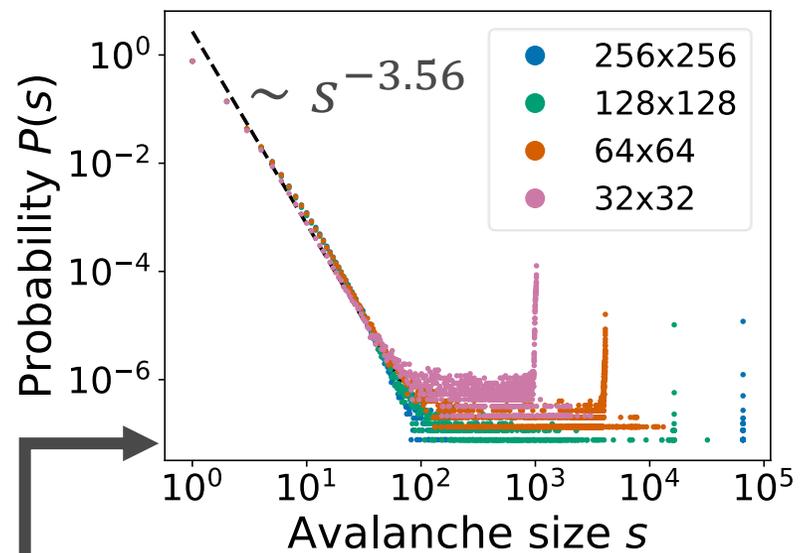
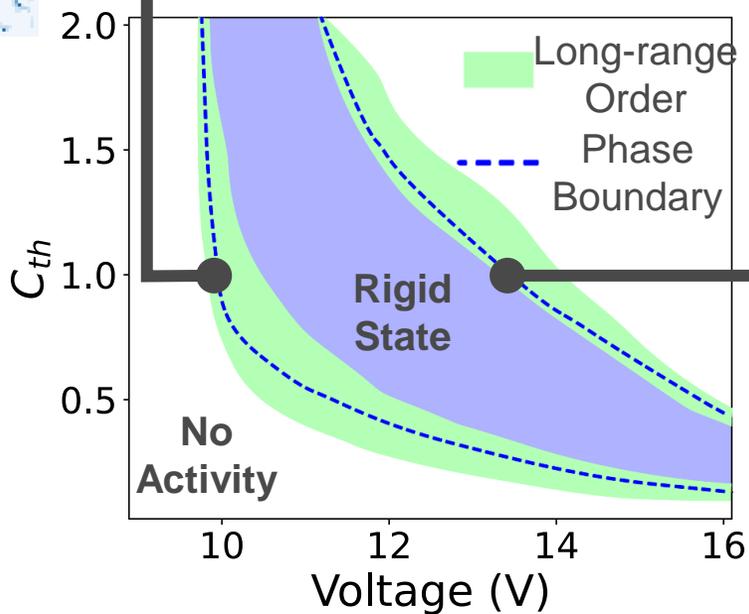
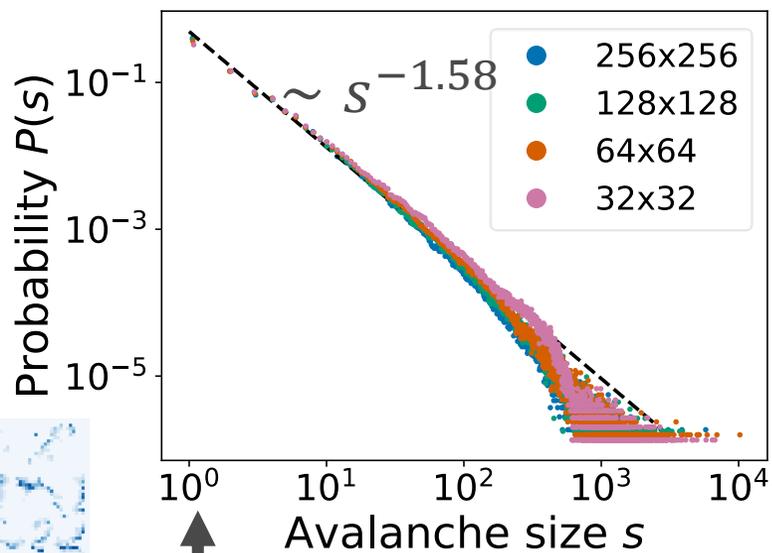
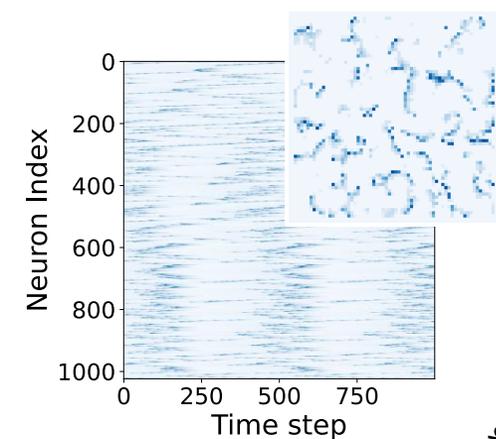






# Long-range order?



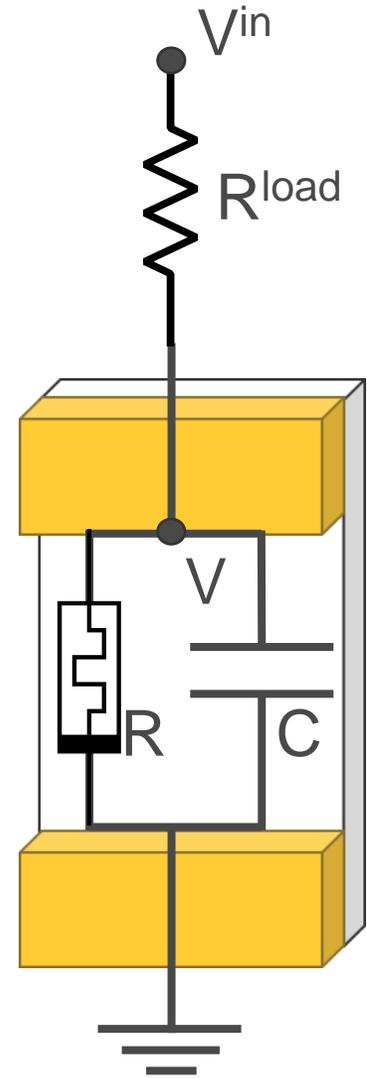
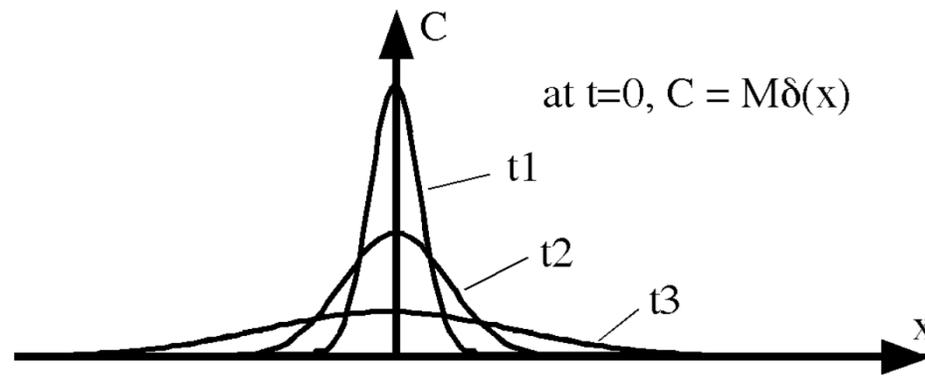
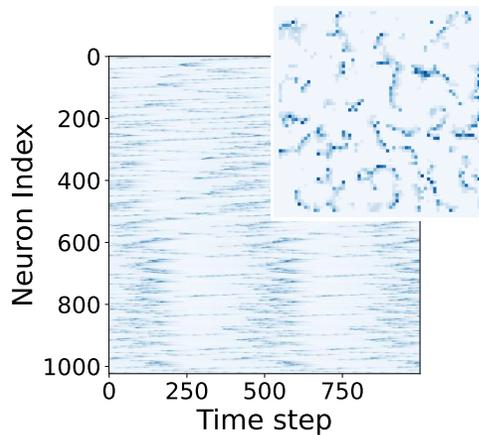




# Long-range order?

$$C \frac{dV}{dt} = \frac{V_{in}}{R_{load}} - V \left( \frac{1}{R_{VO_2}} + \frac{1}{R_{load}} \right)$$

$$C_{th} \frac{dT}{dt} = \frac{V^2}{R_{VO_2}} - S_{env}(T - T_0) + S_{couple} \nabla^2 T + \eta(t)$$





# Memory-induced long-range order

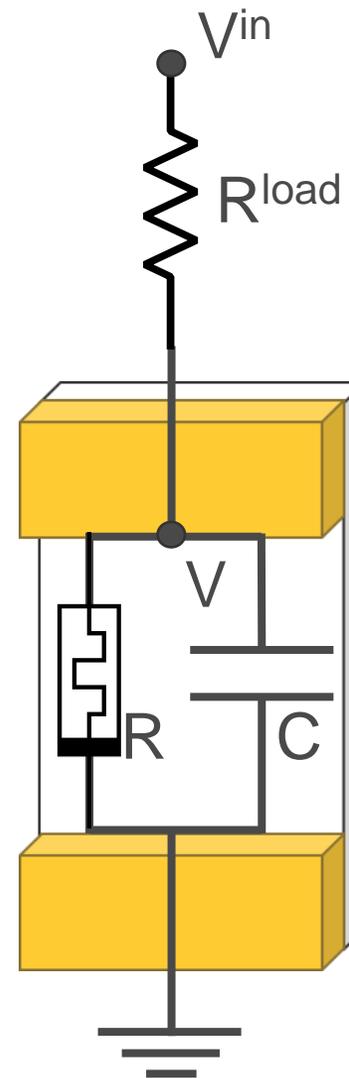
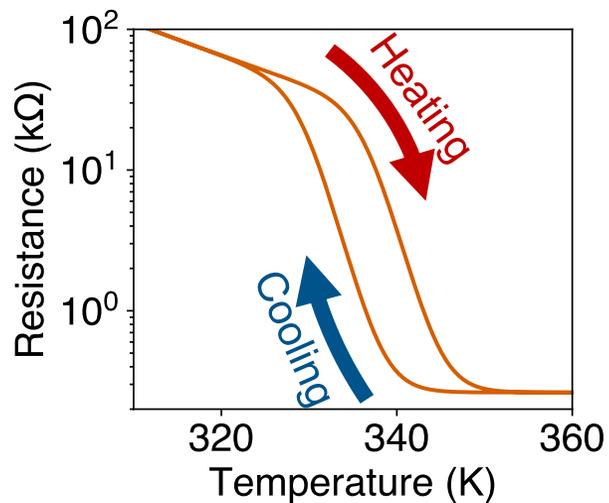
Charge / Heat  
Accumulation

$$C \frac{dV}{dt} = \frac{V_{in}}{R_{load}} - V \left( \frac{1}{R_{VO_2}} + \frac{1}{R_{load}} \right)$$

$$C_{th} \frac{dT}{dt} = \frac{V^2}{R_{VO_2}} - S_{env}(T - T_0) + S_{couple} \nabla^2 T + \eta(t)$$

Hysteresis

Memory





# Memory-induced long-range order

$$C \frac{dV}{dt} = \frac{V_{in}}{R_{load}} - V \left( \frac{1}{R_{VO_2}} + \frac{1}{R_{load}} \right)$$

$$C_{th} \frac{dT}{dt} = \frac{V^2}{R_{VO_2}} - S_{env}(T - T_0) + S_{couple} \nabla^2 T + \eta(t)$$

Slow charging / heating

$$\tau_{ins} = R_{ins} C \sim 7.6 \mu s$$

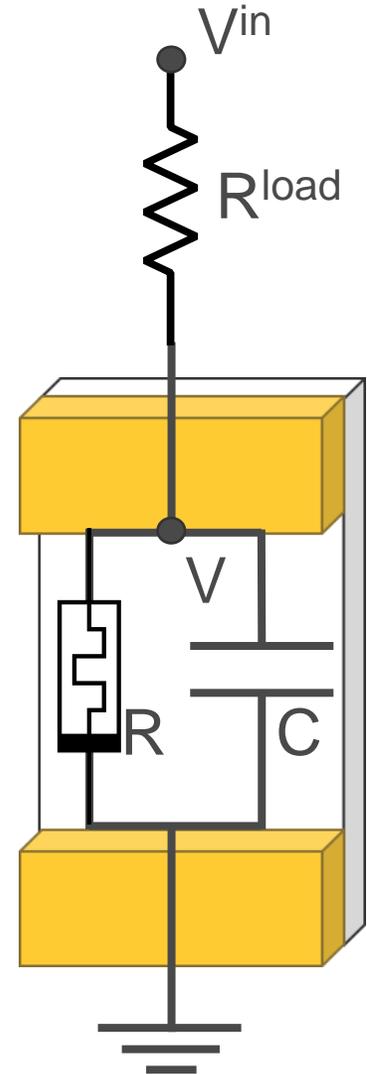
$$\tau_T = C_{th} / S_{couple} \sim 12 \mu s$$

Fast spiking / dissipation

$$\tau_{met} = R_{met} C \sim 190 ns$$

$$\tau_{th} = C_{th} / S_{env} \sim 240 ns$$

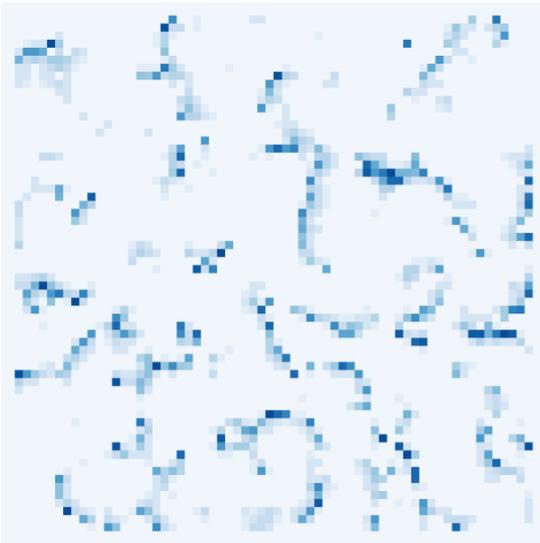
Separation of  
time scales





# Memory-induced long-range order

Thermal neuristors



Sandpile model:  
Self-organized criticality

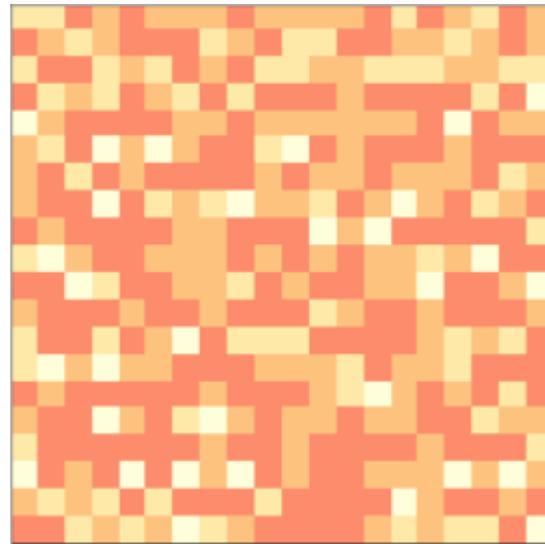


Image credit:

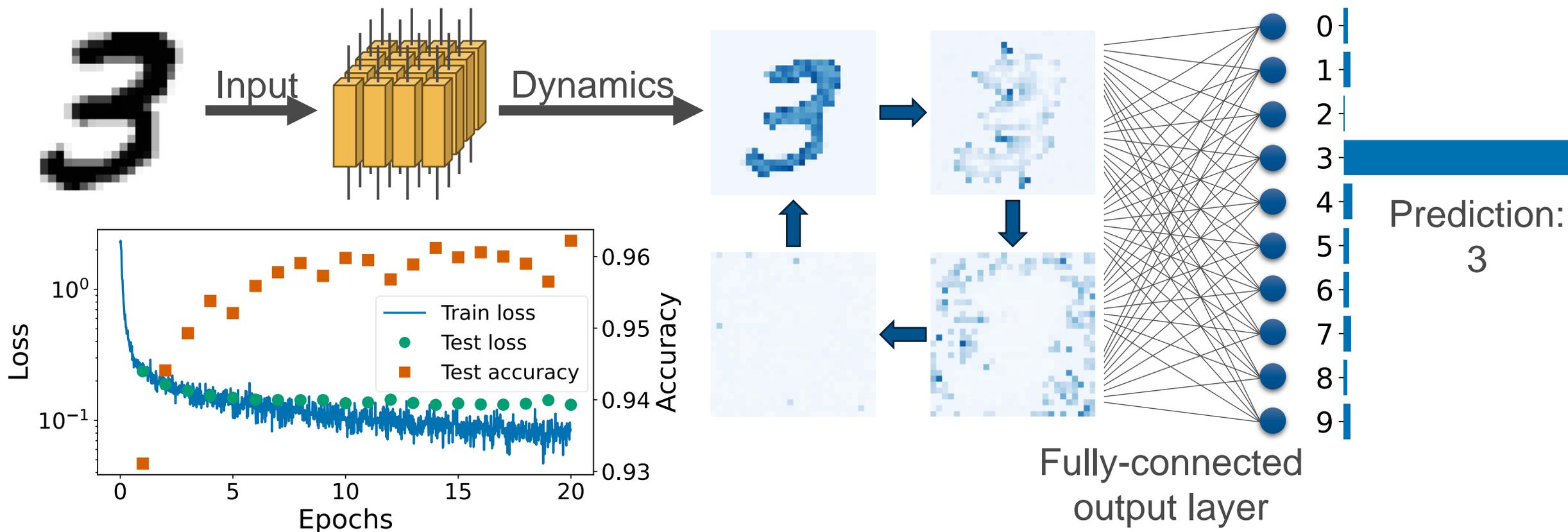
<https://runestone.academy/ns/books/published/complex/SelfOrganizedCriticality/ImplementingTheSandPile.html>



Bak, Per, Chao Tang, and Kurt Wiesenfeld. "Self-organized criticality: An explanation of the  $1/f$  noise." *Physical review letters* 59.4 (1987): 381.  
Hesse, Janina, and Thilo Gross. "Self-organized criticality as a fundamental property of neural systems." *Frontiers in systems neuroscience* 8 (2014): 166.



# Application: MNIST

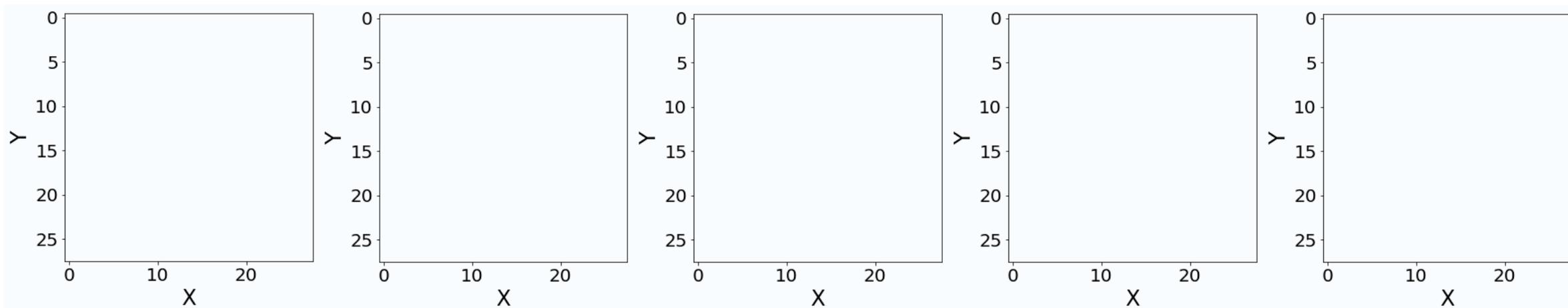
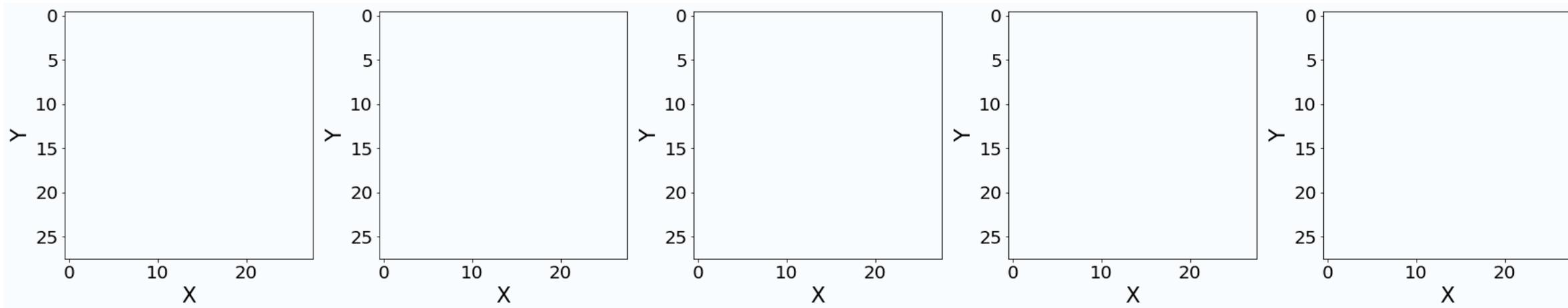




# Application: MNIST

Rigid State

LRO is not  
necessary!





# Conclusions

- Spiking oscillators utilizing insulator-to-metal transition in  $\text{VO}_2$
- Phase of memory-induced long-range order
- Application to reservoir computing



# Thank you!

Y.-H. Zhang, C. Sipling, E. Qiu, I. K. Schuller, M. Di Ventra, Collective dynamics and long-range order in thermal neuristor networks. arXiv preprint arXiv:2312.12899

E. Qiu, Y.-H. Zhang, M. Di Ventra, I. K. Schuller, Reconfigurable cascaded thermal neuristors for neuromorphic computing. *Advanced Materials*, 2306818.

Looking for postdoc positions!



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